

Fig. 1. Schematic diagrams of (a) sample layer structure of three cycles of the InGaAs/GaAsSb/InGaAs W-QW and (b) band alignment of one cycle of the W-QW with GaAsP strain-compensation layers.

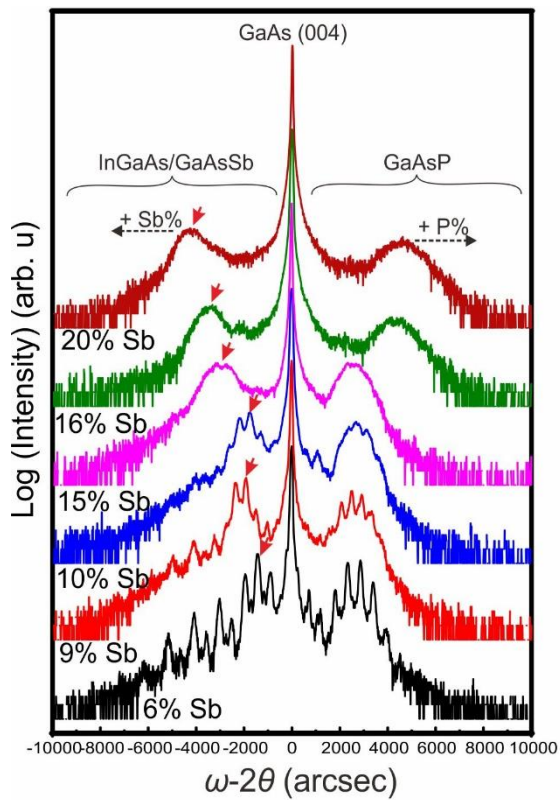


Fig. 2. X-ray rocking curves of W-QW with various Sb compositions in the GaAsSb layer. The red arrows show the shift of the rocking curves as a function of different Sb compositions.

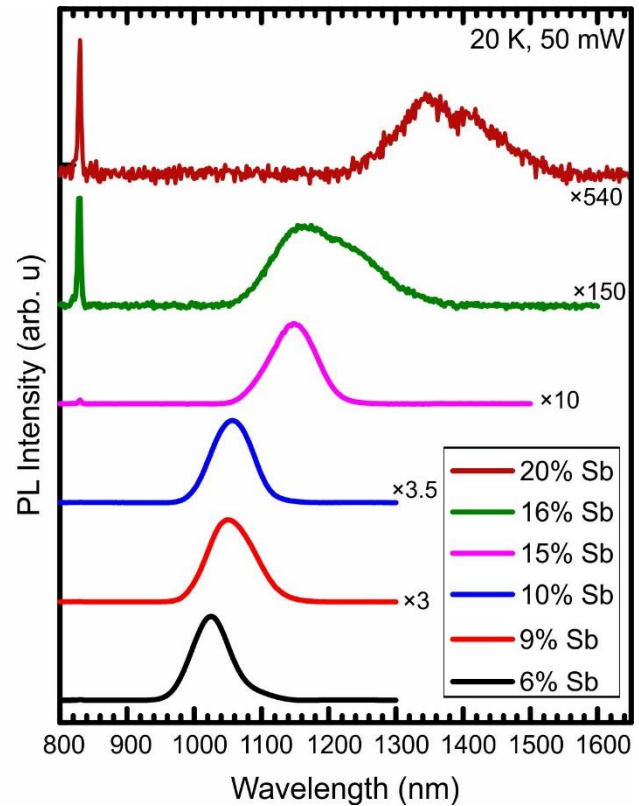


Fig. 3. Low-temperature PL (excitation power of 50 mW) of W-QW with various Sb compositions. The spectra are shifted vertically for clarity.